

Supporting Information

Improving power factor and figure of merit of p-type CuSbSe₂ via introducing Sb vacancies

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1. The density(d) and the relative density(d_r) of $\text{CuSb}_{1-x}\text{Se}_2$ ($x=0-0.12$)

Table S1. The density(d) and the relative density(d_r) of $\text{CuSb}_{1-x}\text{Se}_2$ ($x=0-0.12$)

$\text{CuSb}_{1-x}\text{Se}_2$	d (g cm ³)	d_r (%)
$x=0$	5.71	97.1
$x=0.03$	5.85	99.4
$x=0.06$	5.86	99.6
$x=0.09$	5.84	99.3
$x=0.12$	5.85	99.4

2. The temperature dependence of C_p for $\text{CuSb}_{1-x}\text{Se}_2$ ($x=0-0.12$) samples.

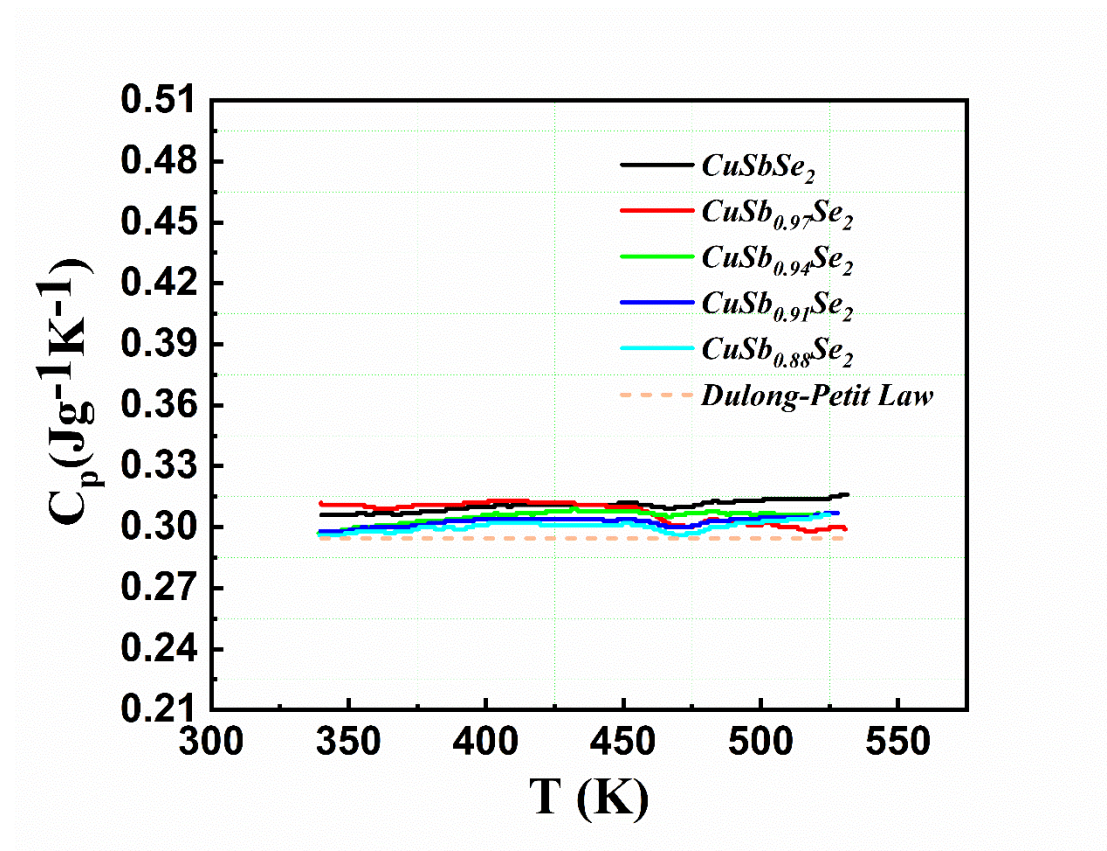


Figure S1. The temperature dependence of C_p for $\text{CuSb}_{1-x}\text{Se}_2$ ($x=0-0.12$) samples.

3. EDAX measurement for all samples of $\text{CuSb}_{1-x}\text{Se}_2$ ($x=0, 0.03, 0.06, 0.09$ and 0.12).

Table S2 Compositions of all samples measured with EDAX.

	Cu (At%)	Sb (At%)	Se (At%)
CuSbSe_2	27.5	26.3	46.2
$\text{CuSb}_{0.97}\text{Se}_2$	27.6	26.1	46.3
$\text{CuSb}_{0.94}\text{Se}_2$	28.0	25.7	46.4
$\text{CuSb}_{0.91}\text{Se}_2$	28.6	25.6	45.8
$\text{CuSb}_{0.88}\text{Se}_2$	29.1	24.5	46.4